TGA2958-SM

13 – 18 GHz 2 W GaN Driver Amplifier

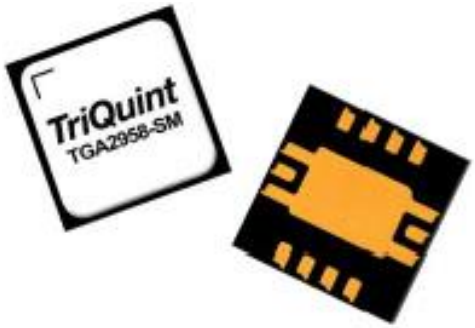
Product Description

The TGA2598-SM is a packaged Ku-band amplifier fabricated on Qorvo's 0.15 um GaN on SiC production process (QGaN15). Operating over a 13 – 18 GHz bandwidth, the TGA2598-SM delivers 2W of saturated output power with 20 dB large signal gain and > 25 % power-added efficiency. This, along with >25 dB small signal gain allows it to support a variety of low power Ku-band systems or as a linear, high-voltage driver for Qorvo's line of high power Ku-band amplifiers.

Packaged in a 4 x 4 air-cavity QFN package for high performance and easy handling, the TGA2958-SM is fully matched to 50 ohms with integrated DC blocking capacitors on both I/O ports for simple system integration. This makes for an ideal general purpose RF amplifier which can provide needed functionality across both commercial and defense related markets.

Lead free and RoHS compliant.

Evaluation Boards are available upon request.

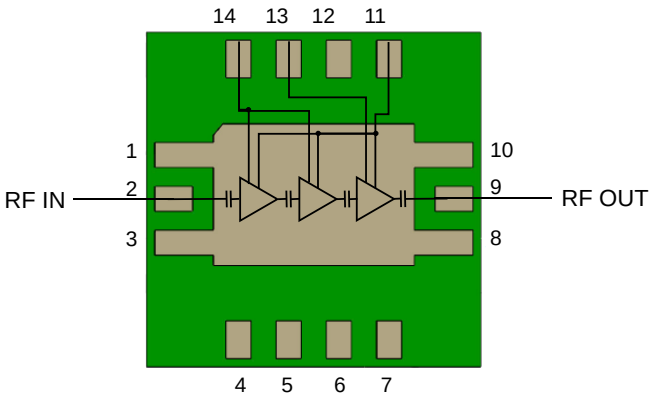


Product Features

- Frequency Range: 13 – 18 GHz
- P_{SAT}: 33 dBm at P_{IN} = 13 dBm
- PAE: 25 % at P_{IN} = 13 dBm
- Small Signal Gain: 25 dB
- Input Return Loss: > 7 dB
- Output Return Loss: > 13 dB
- Bias: V_D = +20 V, I_{DQ} = 70 mA, V_G = −2.7 V Typical
- Package Dimensions: 4.0 x 4.0 x 1.74 mm
- Performance under CW operation

Performance is typical across frequency. Please reference electrical specification table and data plots for more details.

Functional Block Diagram



Applications

- Satellite Communications
- Data Links
- Radar
- General Purpose

Ordering Information

Part No.	ECC	Description
TGA2958-SM	EAR99	13 – 18 GHz 2 W GaN Driver Amplifier

Electrical Specifications

Parameter	Freq. (GHz)	Min	Typ	Max	Units
Operational Frequency Range		13	–	18	GHz
Small Signal Gain			25		dB
Input Return Loss			> 7		dB
Output Return Loss			> 13		dB
Output Power at P_{IN} = 13 dBm	13	31	32.5		dBm
	14, 15, 16, 17	32.5	34		
	18	31.5	33		
Power Added Efficiency at P_{IN} = 13 dBm	13	16	22		%
	14, 15, 16, 17	19	28		
	18	17	23		
Large Signal Gain at P_{IN} = 13 dBm			> 20		dB
IM3 (Pout/tone = 24 dBm, 1 MHz spacing)			−31		dBc
IM5 (Pout/tone = 24 dBm, 1 MHz spacing)			−46		dBc
Small Signal Gain Temperature Coefficient			−0.07		dB/°C
Output Power Temperature Coefficient - at P_{IN} = 0 dBm - at P_{IN} = 12 dBm			 −0.04 −0.01		dB/°C

Test conditions unless otherwise noted: 25 °C, V_D = +20 V, I_{DQ} = 70 mA, V_G = −2.7 V Typ, CW

Recommended Operating Conditions

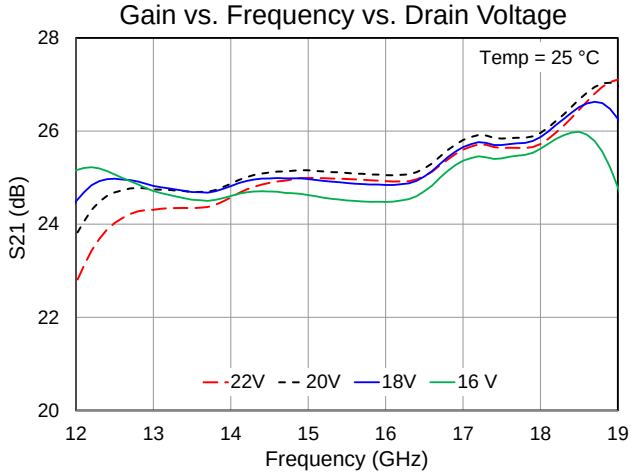
Parameter	Value / Range
Drain Voltage (V_D) CW	20 - 22 V
Drain Current (I_{DQ})	70 mA
Drain Current Under RF Drive (I_{D_DRIVE})	See plots p. 7
Gate Voltage (V_G)	−2.7 V (Typ.)
Gate Current Under RF Drive (I_{G_DRIVE})	See plots p. 7
Temperature (T_{BASE})	−40 to 85 °C

Electrical specifications are measured at specified test conditions. Specifications are not guaranteed over all recommended operating conditions.

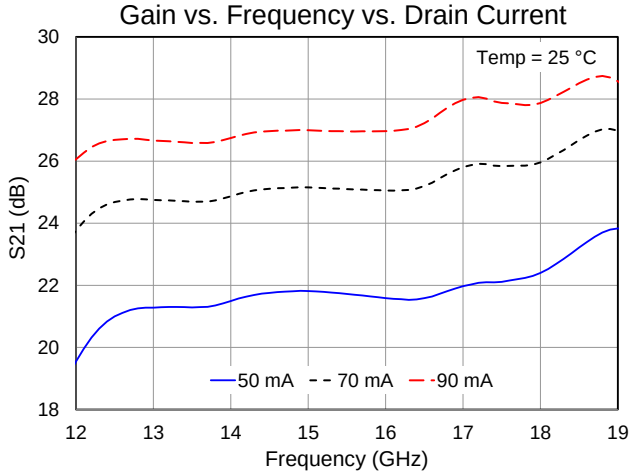
Typical Performance – Small Signal

Conditions unless otherwise specified: V_D = +20 V, I_{DQ} = 70 mA, V_G = −2.7 V Typ, CW

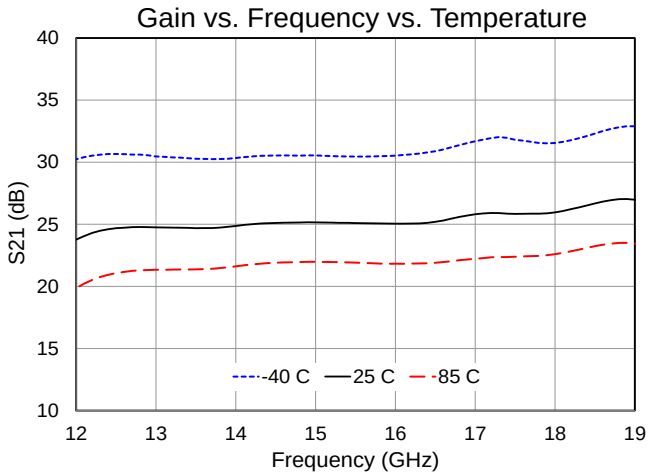
Gain vs. Frequency vs. Drain Voltage



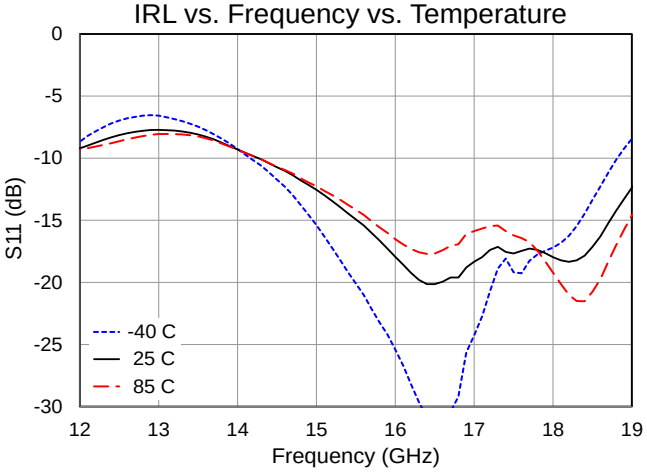
Gain vs. Frequency vs. Drain Current



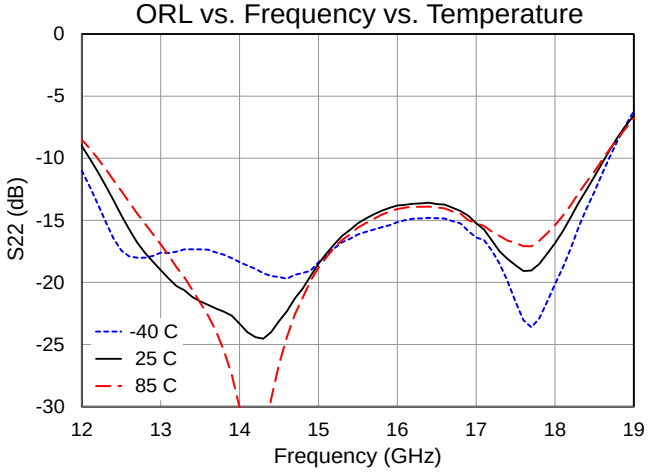
Gain vs. Frequency vs. Temperature



IRL vs. Frequency vs. Temperature



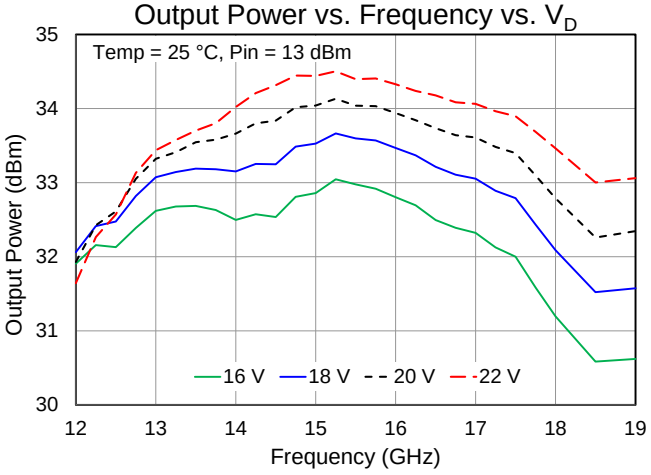
ORL vs. Frequency vs. Temperature



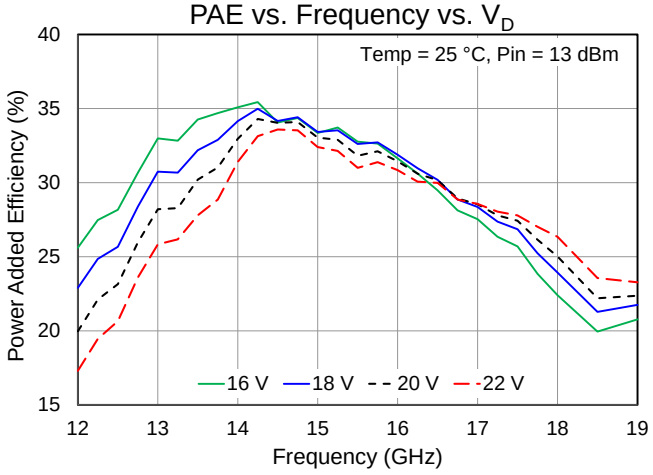
Performance Plots – Large Signal

Conditions unless otherwise specified: V_D = +20 V, I_{DQ} = 70 mA, V_G = −2.7 V Typ, CW

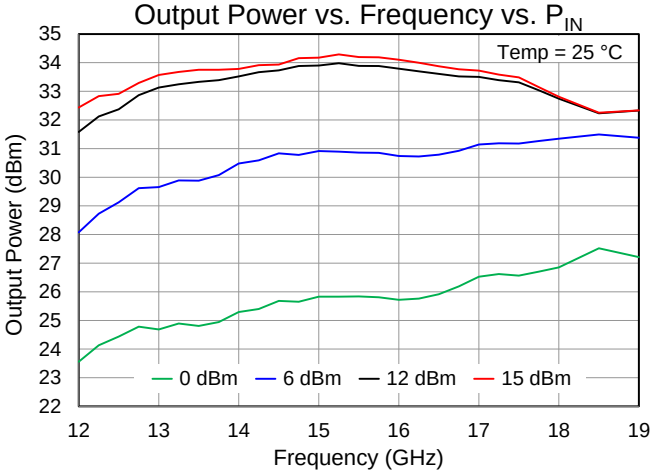
Output Power vs. Frequency vs. V_D



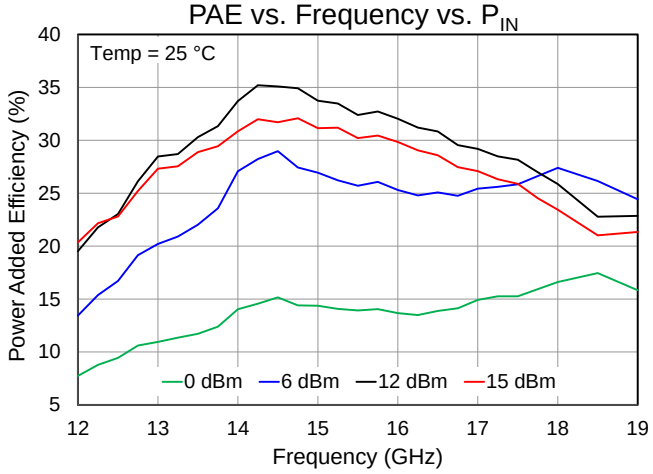
PAE vs. Frequency vs. V_D



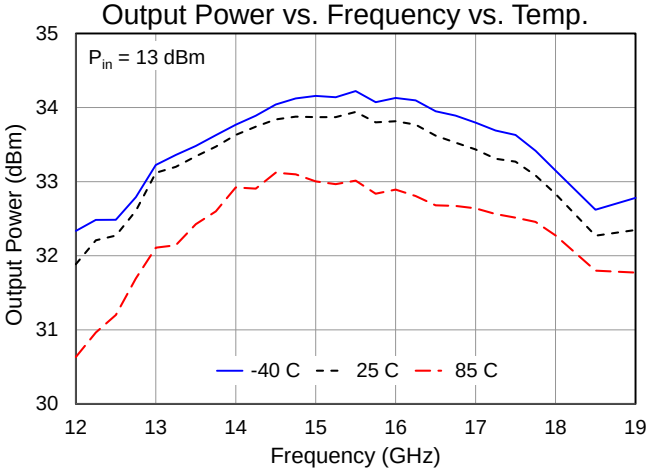
Output Power vs. Frequency vs. P_{IN}



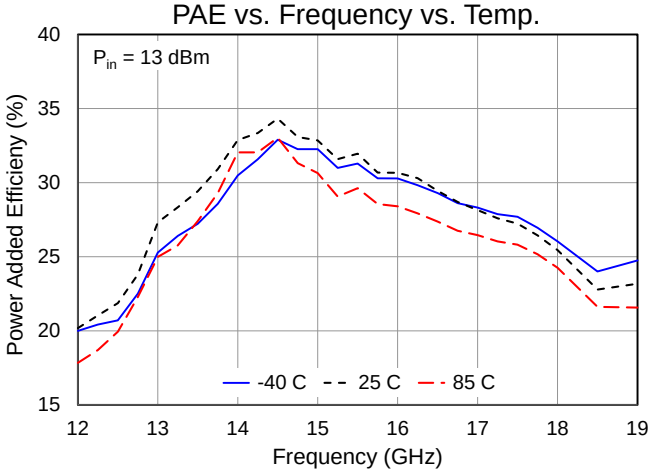
PAE vs. Frequency vs. P_{IN}



Output Power vs. Frequency vs. Temp.



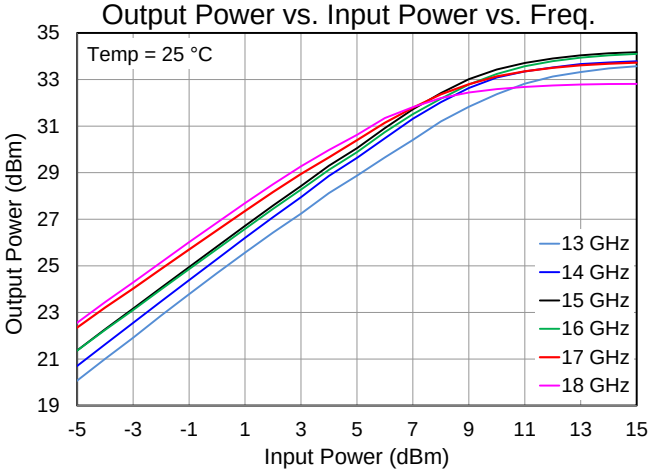
PAE vs. Frequency vs. Temp.



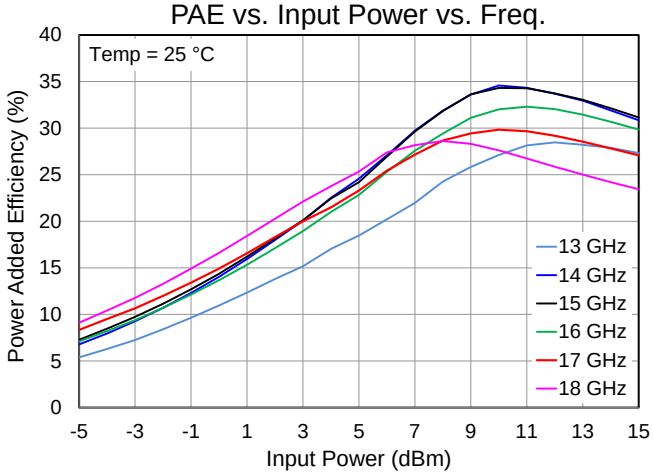
Typical Performance – Large Signal

Conditions unless otherwise specified: V_D = +20 V, I_{DQ} = 70 mA, V_G = −2.7 V Typ, CW

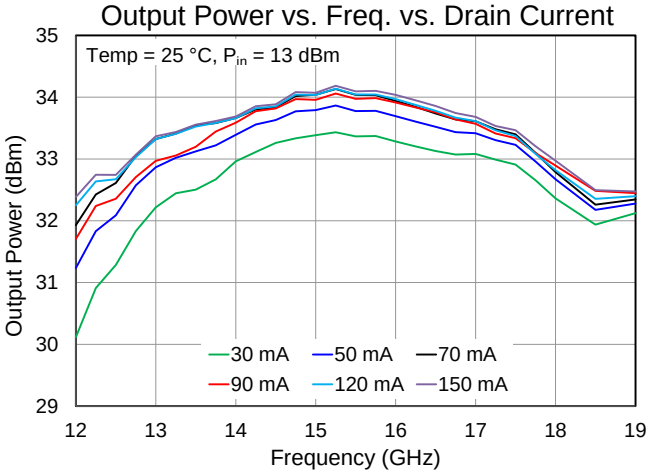
Output Power vs. Input Power vs. Freq.



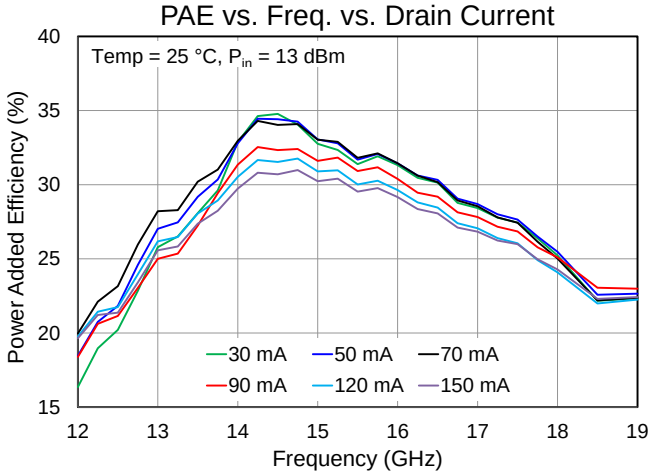
PAE vs. Input Power vs. Freq.



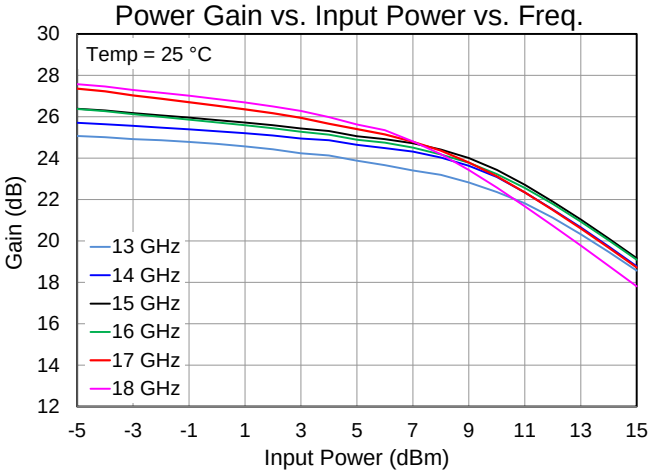
Output Power vs. Freq. vs. Drain Current



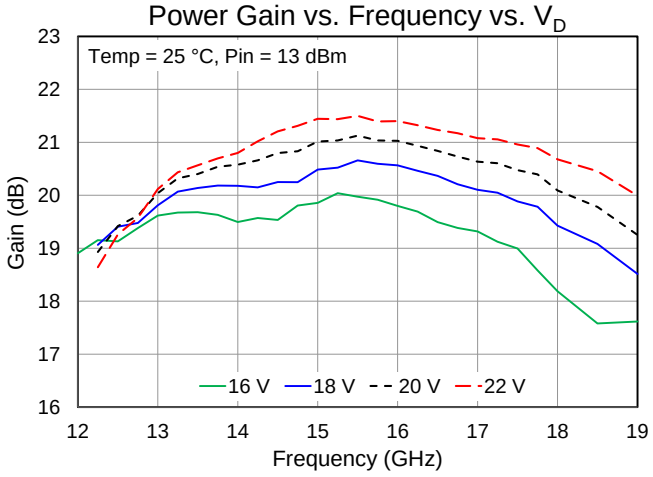
PAE vs. Freq. vs. Drain Current



Power Gain vs. Input Power vs. Freq.

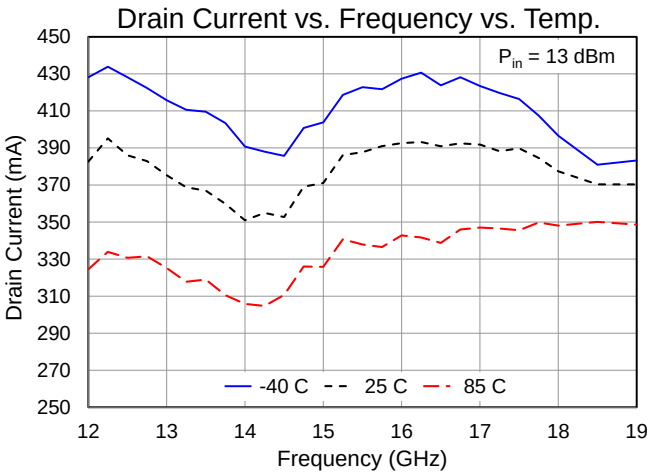


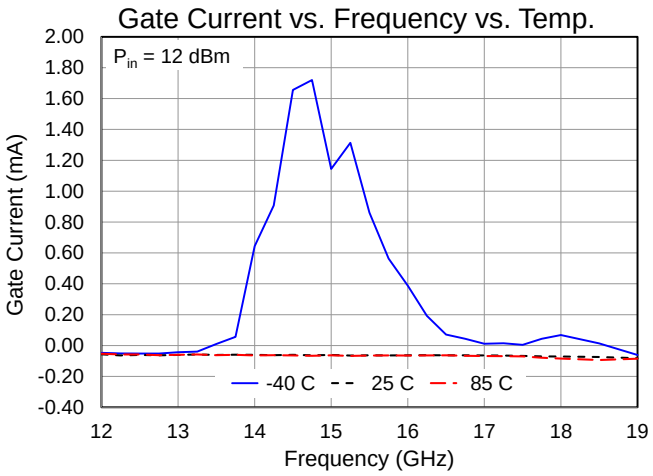
Power Gain vs. Frequency vs. V_D

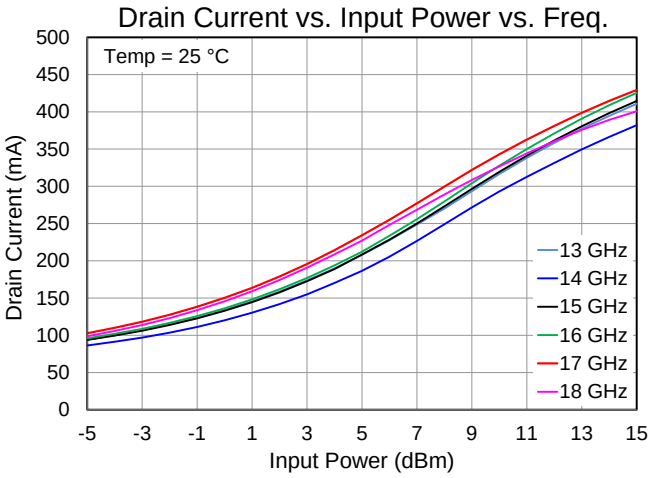


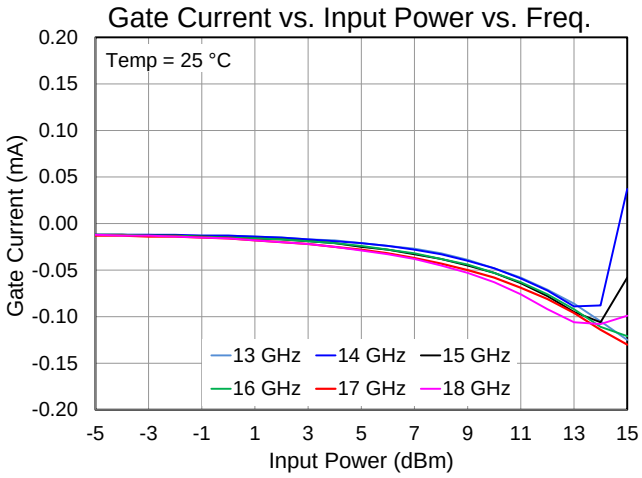
Typical Performance – Large Signal

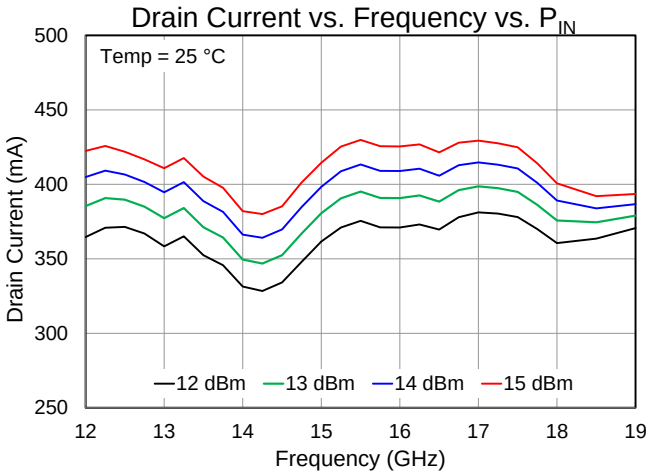
Conditions unless otherwise specified: V_D = +20 V, I_{DQ} = 70 mA, V_G = −2.7 V Typ, CW

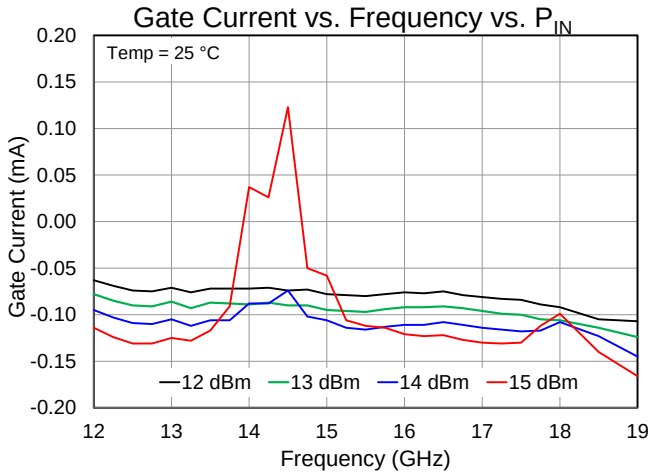






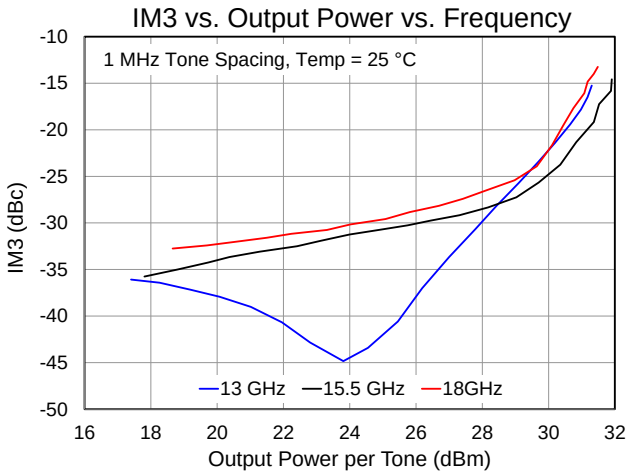


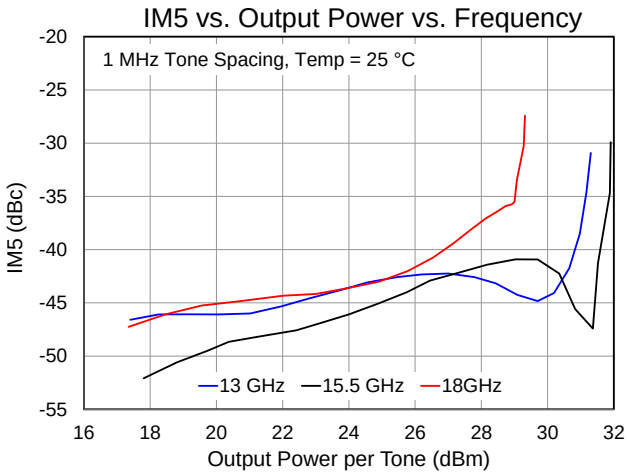


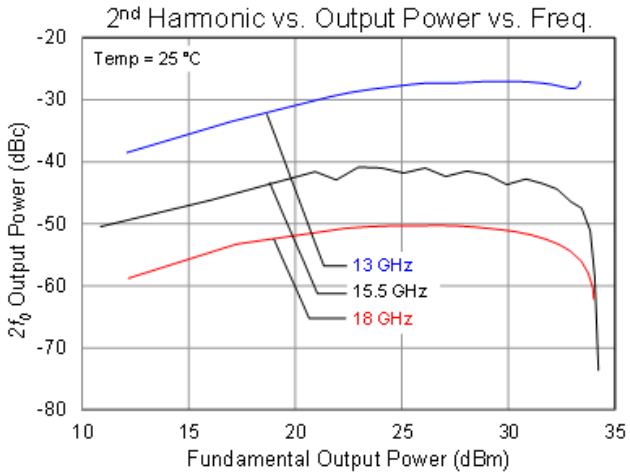


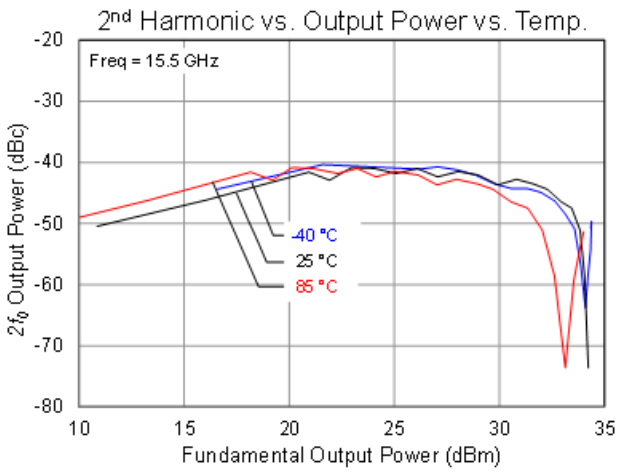
Typical Performance – Linearity

Conditions unless otherwise specified: V_D = +20 V, I_{DQ} = 70 mA, V_G = −2.7 V Typ, CW; harmonic data from die version









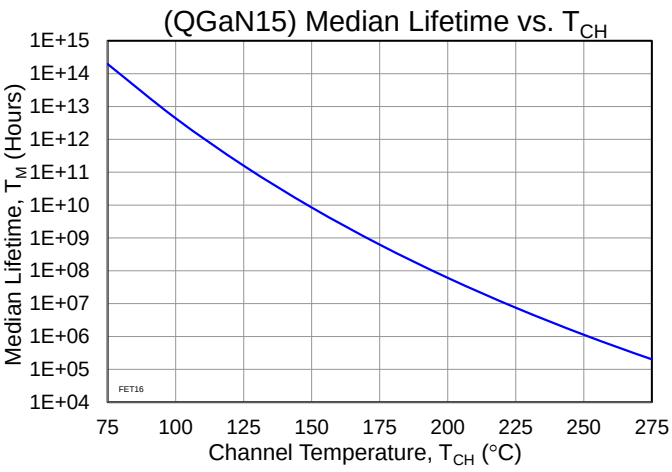
Thermal and Reliability Information

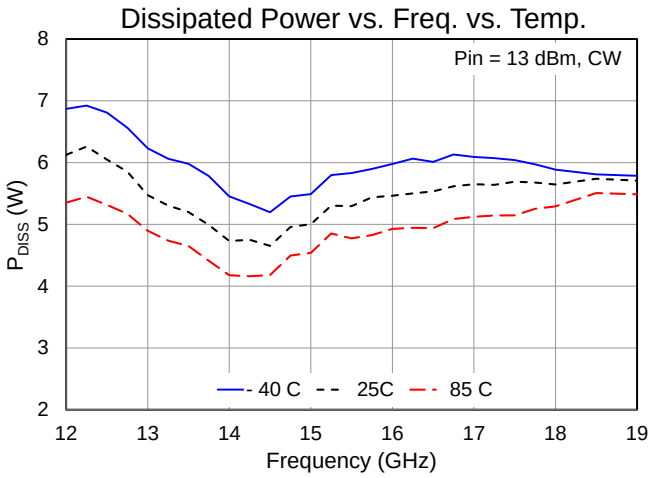
Parameter	Test Conditions	Value	Units
Thermal Resistance (θ_{JC}) (1)	T_{BASE} = 85 °C, V_D = +20 V (CW) At I_{DQ} = 70 mA, P_{DISS} = 1.4 W	10.0	°C/W
Channel Temperature (T_{CH}) (Quiescent)		99	°C
Median Lifetime (T_M)		3.5 x 10^15	Hrs
Thermal Resistance (θ_{JC}) (1)	T_{BASE} = 85 °C, V_D = +20 V (CW) At Freq = 17 GHz, I_{DQ} = 70 mA, P_{OUT} = 27 dBm, P_{DISS} = 2.6 W	13.8	°C/W
Channel Temperature (T_{CH}) (Under RF drive)		121	°C
Median Lifetime (T_M)		7.7 x 10^13	Hrs
Thermal Resistance (θ_{JC}) (1)	T_{BASE} = 85 °C, V_D = +20 V (CW) At Freq = 17 GHz, I_{DQ} = 70 mA, P_{OUT} = 33.5 dBm, P_{DISS} = 5.3 W	14.9	°C/W
Channel Temperature (T_{CH}) (Under RF drive)		164	°C
Median Lifetime (T_M)		1.3 x 10^11	Hrs

Notes:
1. Thermal resistance measured to back of package.

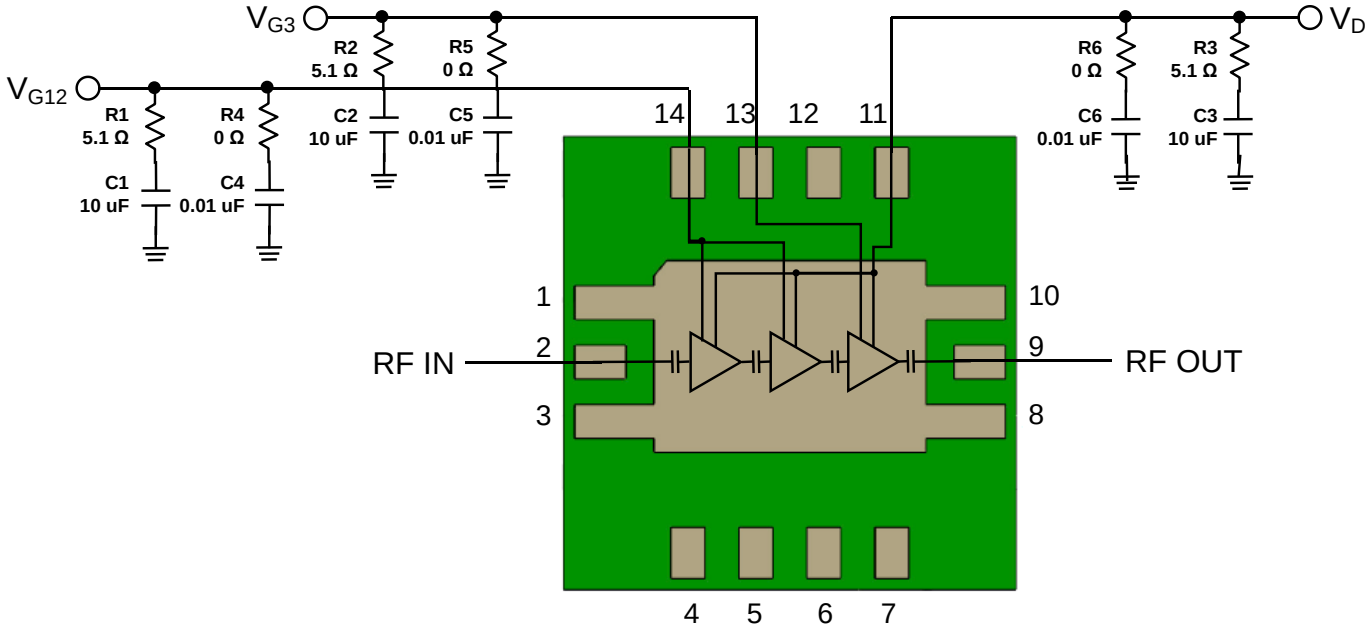
Median Lifetime

Test Conditions: V_D = +28 V; Failure Criteria = 10 % reduction in I_{D_MAX} during DC Life Testing





Application Circuit



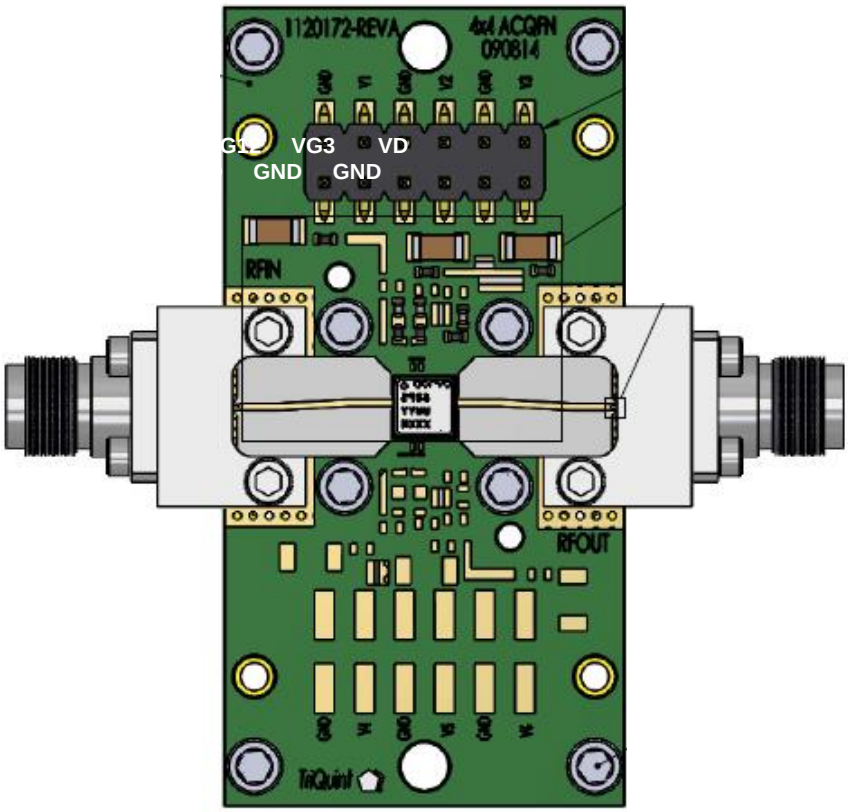
Bias Up Procedure

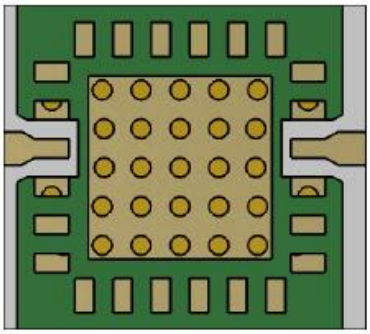
1. Set I_D limit to 500 A, I_G limit to 13 mA
2. Apply −5 V to V_G
3. Apply +20 V to V_D; ensure I_{DQ} is approx. 0 mA
4. Adjust V_G until I_{DQ} = 70 mA (V_G ~ −2.7 V Typ.).
5. Turn on RF signal generator

Bias Down Procedure

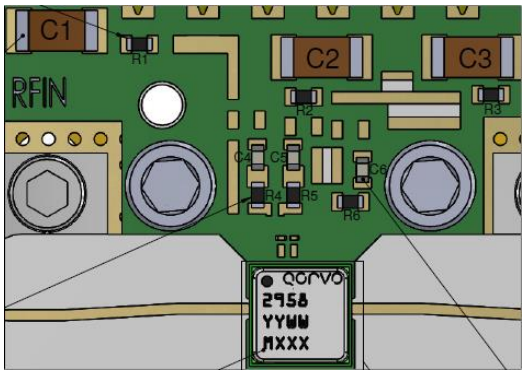
1. Turn off RF signal generator
2. Reduce V_G to −5 V; ensure I_{DQ} is approx. 0 mA
3. Set V_D to 0 V
4. Turn off V_D supply
5. Turn off V_G supply

Evaluation Board





Mounting pad detail



Component placement

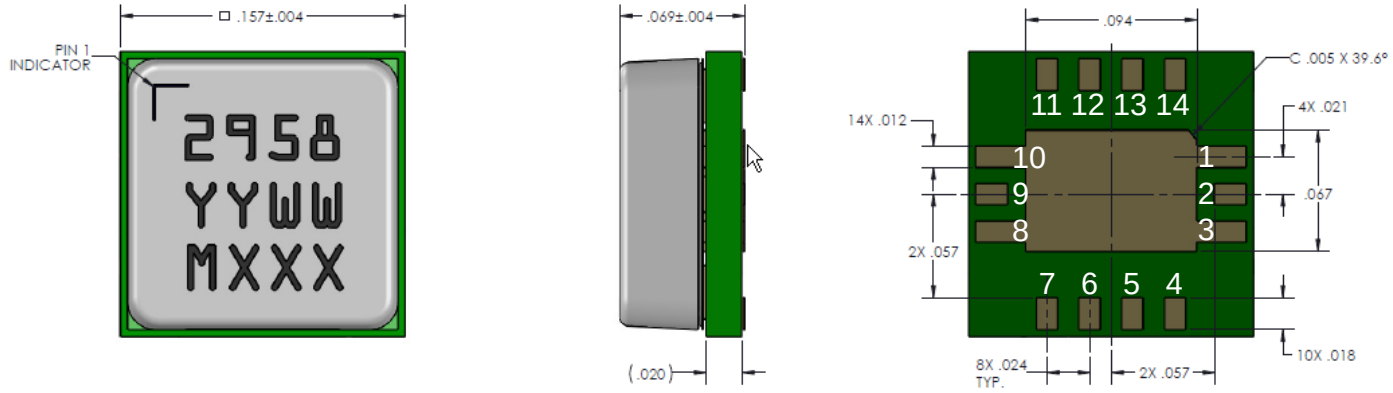
RF Layer is 0.008” thick Rogers Corp. RO4003C, εr = 3.38. Metal layers are 0.5 oz. copper. The microstrip line at the connector interface is optimized for the Southwest Microwave end launch connector 1092-01A-5.

The trace pattern shown has been developed and tested for optimized assembly at TriQuint Semiconductor. The PCB land pattern has been developed to accommodate lead tolerances. Since processes vary from company to company, careful process development is recommended.

Bill of Materials

Reference Des.	Value	Description	Manuf.	Part Number
C1, C2, C3	10 µF	Cap., 1206, +50 V, 20 %, X5R	Various	–
C4, C5, C6	0.01 µF	Cap., 0402, +50 V, 10 %, X7R	Various	–
R1, R2, R3	5.1 Ohms	Res., 0402, 5 %, SMD	Various	–
R4, R5, R6	0.0 Ohms	Res., 0402, 5 %, SMD	Various	–

Mechanical Information



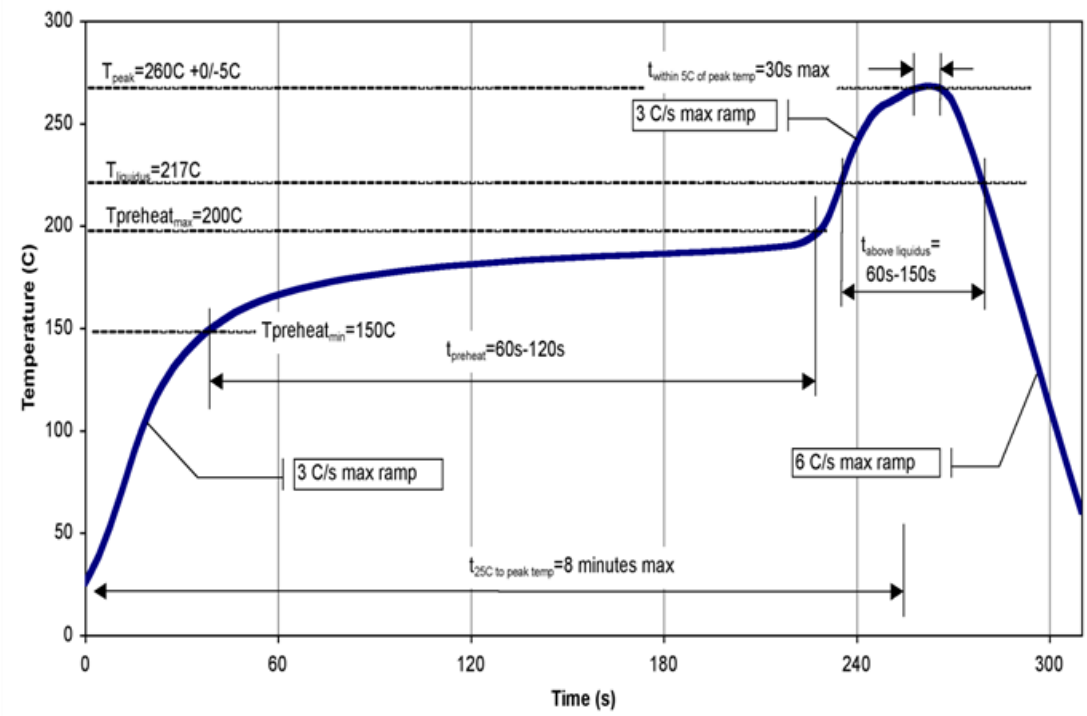
Units: inches
Tolerances: unless specified
x.xx = ± 0.01
x.xxx = ± 0.005
Marking:
2958: Part number
YY: Part Assembly year
WW: Part Assembly week
MXXX: Batch ID

Pad Description

Pad No.	Symbol	Description
1, 3, 8, 10	GND	RF Ground
2	RF_{IN}	RF Input; matched to 50 Ω; DC blocked
4, 5, 6, 7, 12	NC	No connection inside package; pads can be grounded if desired
9	RF_{OUT}	RF Output; matched to 50 Ω; DC blocked
11	V_D	Drain voltage; Bias network is required; see recommended Application Information
13	V_{G3} (1)	Gate Voltage; Bias network is required; see recommended Application Information
14	V_{G12} (1)	Gate Voltage; Bias network is required; see recommended Application Information

Notes:
1. Pads 13 & 14 may be tied together for biasing

Recommended Soldering Temperature Profile



Absolute Maximum Ratings

Parameter	Value / Range
Drain Voltage (V_D)	29.5 V
Gate Voltage Range (V_G)	−8 to 0 V
Drain Current – common drain - 1st Stage (I_{D1}) - 2nd Stage (I_{D2}) - 3rd Stage (I_{D3})	576 mA 72 mA 192 mA 384 mA
Forward Gate Current (I_G)	See I_{G_MAX} plot
Power Dissipation (P_{DISS}), 85 °C	13 W
Input Power (P_{IN}), CW, 50 Ω, V_D = +22 V, I_{DQ} = 70 mA, 85 °C	27 dBm
Input Power (P_{IN}), CW, VSWR 3:1, V_D = +22 V, I_{DQ} = 70 mA, 85 °C	20 dBm
Channel Temperature (T_{CH})	275 °C
Storage Temperature	−55 to 150 °C

Operation of this device outside the parameter ranges given above may cause permanent damage. These are stress ratings only, and functional operation of the device at these conditions is not implied.